

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

ESD73034D-MS

Product specification

Features

- Up to 4 lines protects
- Ultra low junction capacitance (Max value: 0.35pF)
- Peak Pulse Current (8/20 μ s) MAX: 6A
- IEC61000-4-2 (ESD) $\pm$ 25kV (air), $\pm$ 15kV (contact)
- Low clamping voltage
- Low leakage current
- Working voltages:3.3V
- RoHS Compliant

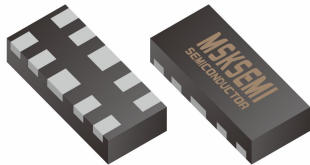
Mechanical Characteristics

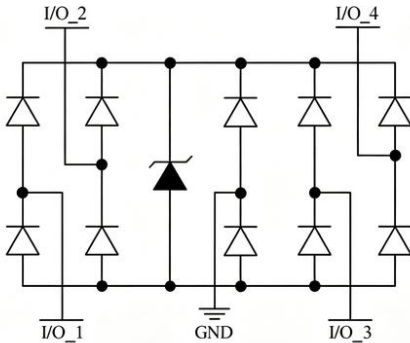
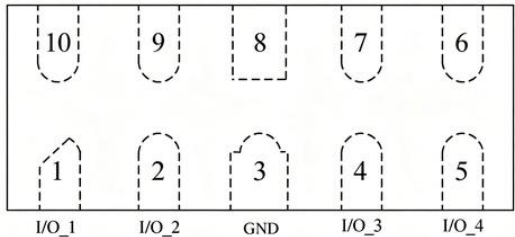
- Package: DFN2510-10L
- Lead Finish: Matte Tin
- Case Material: "Gre en" Molding Compound.
- UL Flammability Classification Rating94V-0
- Moisture Sensitivity: Level 3 per J-STD-020

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation,Digital Cameras
- Peripherals, Audio Players, Industrial Equipment
- Automotive

Reference News

DFN2510-10L	MARKING
	

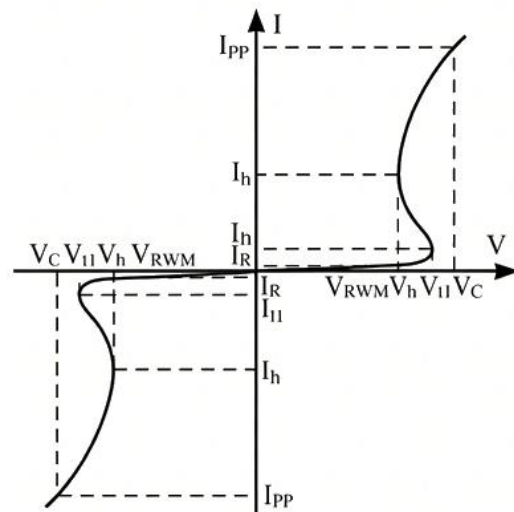
CIRCUIT DIAGRAM	PIN CONFIGURATION
	

Absolute Maximum Ratings (T=25°C, RH=45%-75%, unless otherwise noted)

Parameters	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P _{pp}	60	W
Peak Pulse Current (8/20μs)	I _{PP}	6	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±15 ±8	KV
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Electrical characteristics (T=25°C)

Symbol	Parameter
V _{RWM}	Nominal Reverse Working Voltage
I _R	Reverse Leakage Current @V _{RWM}
V _{t1}	Trigger Voltage
I _{t1}	Trigger Current @V _{t1}
V _h	Holding Voltage
I _h	Holding Current @V _h
V _C	Clamping Voltage @I _{PP}
I _{PP}	Maximum Peak Pulse Current
V _F	Forward Voltage @I _F
C _{ESD}	Parasitic Capacitance
a _{IL}	Insertion Loss
f _{3db}	Cut-off frequency at-3dB



Electrical Characteristics (TA=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				3.3	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	3.8			V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3\text{ V}$			1	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 x 20 μs pulse), any I/O pin to ground		5.8	7.5	V
Clamping Voltage	V_C	$I_{PP} = 6\text{A}$ (8 x 20 μs pulse), any I/O pin to ground		7	10	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$, between I/O pins		0.12	0.2	pF
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$, any I/O pin to ground		0.2	0.35	pF

Typical Characteristics

FIG1: Power rating derating curve

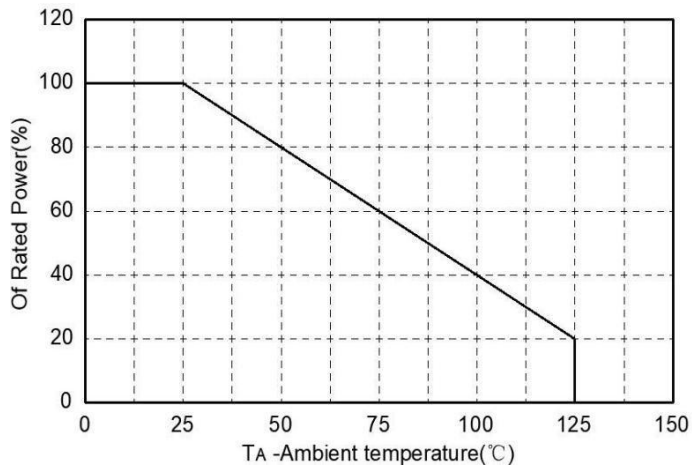


FIG2: pulse Waveform

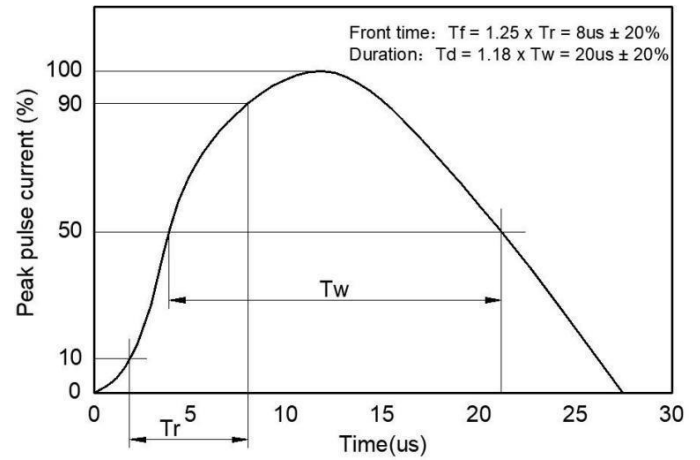


FIG3: TLP CURVE

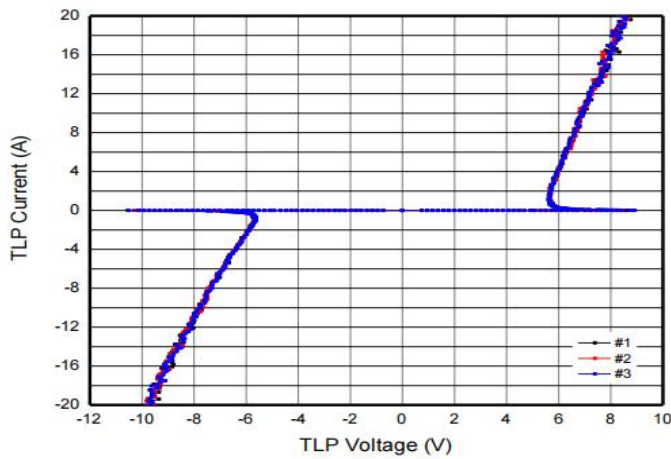
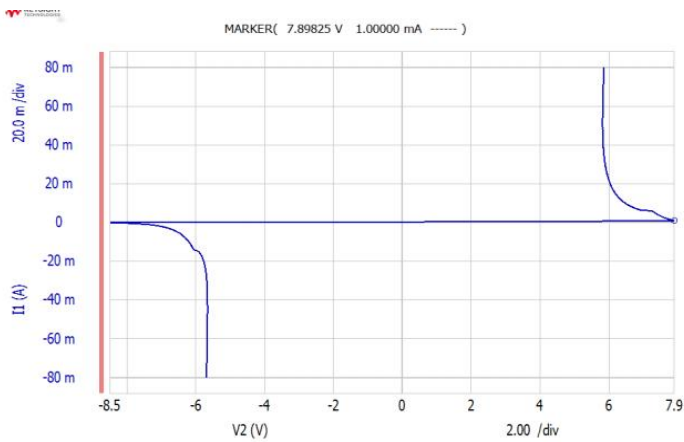
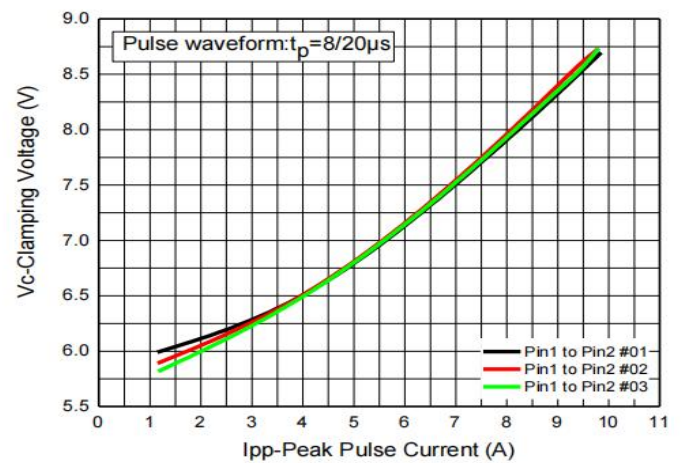
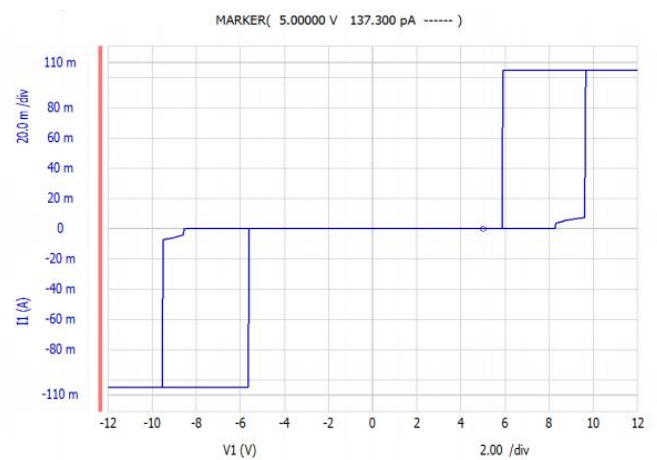


Figure 4: Clamping Voltage vs. Peak Pulse Current



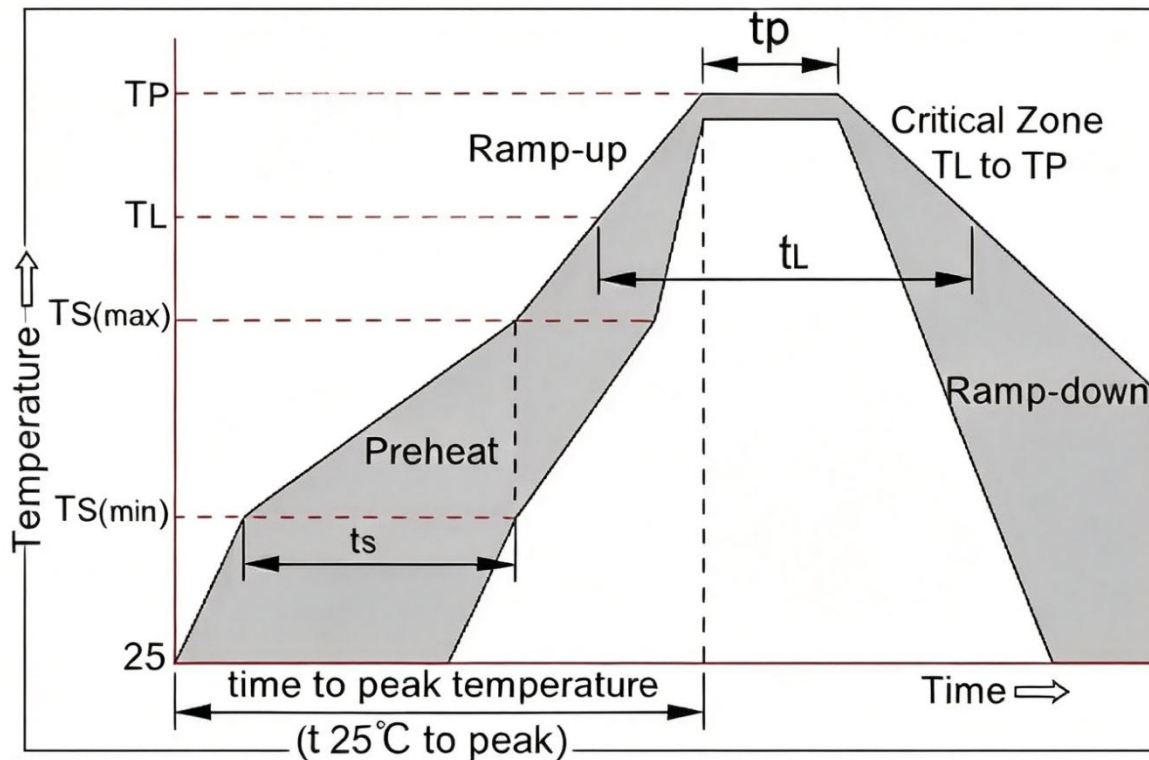
I-V Curve current sweep from -80mA to 80mA



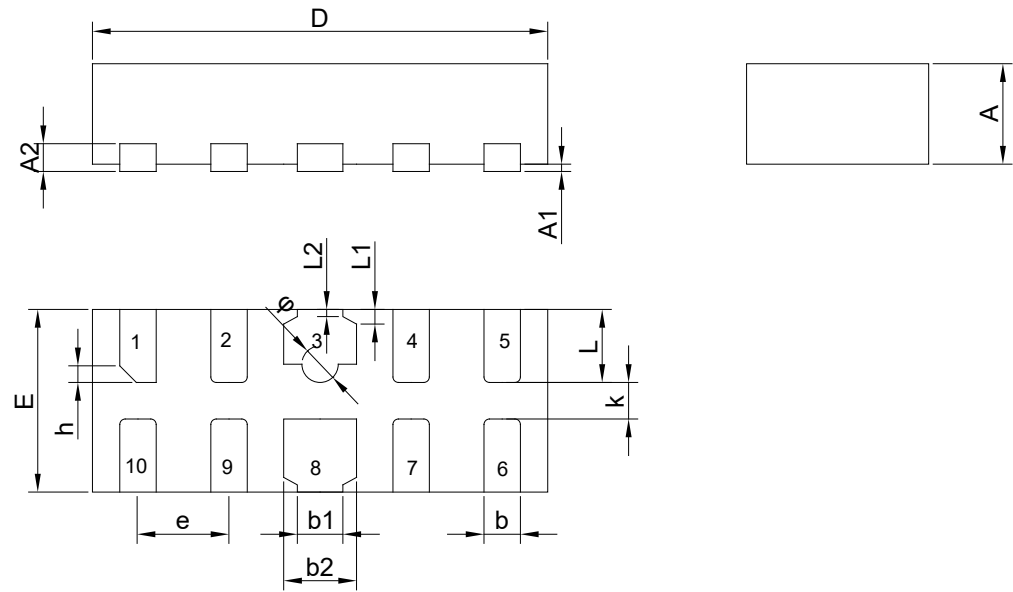
I-V Curve voltage sweep from -12V to 12V

Soldering Parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C



Dimension (DFN2510)



Dimensions in Millimeter							
Symbol	Min.	Nom.	Max.	Symbol	Min.	Nom.	Max.
A	0.500	0.550	0.600	D	2.450	2.500	2.550
A1	0.00	/	0.05	E	0.950	1.00	1.050
A2	0.122	0.152	0.200	e	0.450	0.500	0.550
b	0.150	0.200	0.250	h	0.080	0.120	0.150
b1	0.200	0.250	0.300	k	0.150	0.200	0.250
b2	0.350	0.400	0.450	L	0.350	0.400	0.450
L1	0.075 REF			L2	0.05 REF		
ϕ	0.150	0.200	0.250				

REEL SPECIFICATION

P/N	PKG	QTY
ESD73034D-MS	DFN2510-10L	3000

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specification of any and all MSKSEMI Semiconductor products described or contained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.